# THE DATASHEET OF

# AT28C16-20PI

www.win-source.net 0086-755-83957316

# 16K (2K x 8) CMOS $E^2$PROM

## Features

- Fast Read Access Time - 150 ns
- Fast Byte Write - 200 µs or 1 ms
- Self-Timed Byte Write Cycle
  - Internal Address and Data Latches
  - Internal Control Timer
  - Automatic Clear Before Write
- Direct Microprocessor Control
  - $\overline{\text{DATA}}$ POLLING
- Low Power
  - 30 mA Active Current
  - 100 µA CMOS Standby Current
- High Reliability
  - Endurance: $10^4$ or $10^5$ cycles
  - Data Retention: 10 years
- 5 V ± 10% Supply
- CMOS & TTL Compatible Inputs and Outputs
- JEDEC Approved Byte Wide Pinout
- Full Military, Commercial, and Industrial Temperature Ranges

## Description

The AT28C16 is a low-power, high-performance Electrically Erasable and Programmable Read Only Memory with easy to use features. The AT28C16 is a 16K memory organized as 2,048 words x 8 bits. The device is manufactured with Atmel's reliable non-volatile CMOS technology.

The AT28C16 is accessed like a static RAM for the read or write cycles without the need of external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The end of a write cycle can be determined by $\overline{\text{DATA}}$ polling of $I/O_7$. Once the end of a write cycle has been detected, a new access for a read or a write can begin.

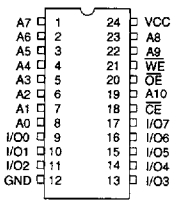
The CMOS technology offers fast access times of 150 ns at low power dissipation. When the chip is deselected the standby current is less than 100 µA.

Atmel's 28C16 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of $E^2$PROM are available for device identification or tracking.

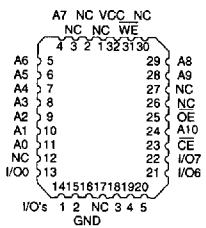
## Pin Configurations

| Pin Name | Function |
|---|---|
| A0 - A10 | Addresses |
| $\overline{\text{CE}}$ | Chip Enable |
| $\overline{\text{OE}}$ | Output Enable |
| $\overline{\text{WE}}$ | Write Enable |
| I/O0 - I/O7 | Data Inputs/Outputs |
| NC | No Connect |

CERDIP, PDIP, SOIC
Top View




PLCC
Top View




Note: PLCC package pins 1 and 17 are DON'T CONNECT.



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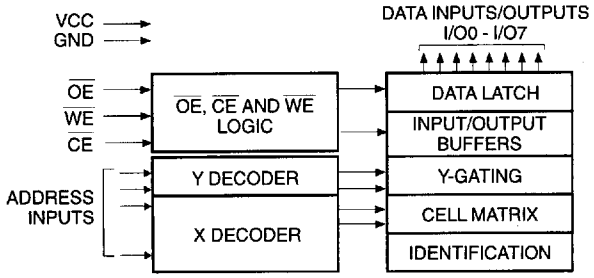
## Block Diagram




## Absolute Maximum Ratings*

| | |
|---|---|
| Temperature Under Bias | -55°C to +125°C |
| Storage Temperature | -65°C to +150°C |
| All Input Voltages (including N.C. Pins) with Respect to Ground | -0.6 V to +6.25 V |
| All Output Voltages with Respect to Ground | -0.6 V to $V_{CC}$ +0.6 V |
| Voltage on $\overline{OE}$ and A9 with Respect to Ground | -0.6 V to +13.5 V |

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## Device Operation

READ: The AT28C16 is accessed like a Static RAM. When $\overline{CE}$ and $\overline{OE}$ are low and $\overline{WE}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever $\overline{CE}$ or $\overline{OE}$ is high. This dual line control gives designers increased flexibility in preventing bus contention.

BYTE WRITE: Writing data into the AT28C16 is similar to writing into a Static RAM. A low pulse on the $\overline{WE}$ or $\overline{CE}$ input with $\overline{OE}$ high and $\overline{CE}$ or $\overline{WE}$ low (respectively) initiates a byte write. The address location is latched on the last falling edge of $\overline{WE}$ (or $\overline{CE}$); the new data is latched on the first rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion. Once a programming operation has been initiated and for the duration of $t_{WC}$, a read operation will effectively be a polling operation.

FAST BYTE WRITE: The AT28C16E offers a byte write time of 200 µs maximum. This feature allows the entire device to be rewritten in 0.4 seconds.

$\overline{DATA}$ POLLING: The AT28C16 provides $\overline{DATA}$ POLLING to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in the complement of that data for $I/O_7$ (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

WRITE PROTECTION: Inadvertent writes to the device are protected against in the following ways. (a) Vcc sense— if Vcc is below 3.8 V (typical) the write function is inhibited. (b) Vcc power on delay— once Vcc has reached 3.8 V the device will automatically time out 5 ms (typical) before allowing a byte write. (c) Write Inhibit— holding any one of $\overline{OE}$ low, $\overline{CE}$ high or $\overline{WE}$ high inhibits byte write cycles.

CHIP CLEAR: The contents of the entire memory of the AT28C16 may be set to the high state by the CHIP CLEAR operation. By setting $\overline{CE}$ low and $\overline{OE}$ to 12 volts, the chip is cleared when a 10 msec low pulse is applied to $\overline{WE}$.

DEVICE IDENTIFICATION: An extra 32 bytes of $E^2$PROM memory are available to the user for device identification. By raising A9 to 12 ± 0.5 V and using address locations 7E0H to 7FFH the additional bytes may be written to or read from in the same manner as the regular memory array.



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## D.C. and A.C. Operating Range

| | | AT28C16-15 | AT28C16-20 | AT28C16-25 |
|---|---|---|---|---|
| Operating Temperature (Case) | Com. | 0°C - 70°C | 0°C - 70°C | 0°C - 70°C |
| | Ind. | -40°C - 85°C | -40°C - 85°C | -40°C - 85°C |
| | Mil. | -55°C - 125°C | -55°C - 125°C | -55°C - 125°C |
| $V_{CC}$ Power Supply | | 5 V ± 10% | 5 V ± 10% | 5 V ± 10% |



## Operating Modes

| Mode | $\overline{CE}$ | $\overline{OE}$ | $\overline{WE}$ | I/O |
|---|---|---|---|---|
| Read | $V_{IL}$ | $V_{IL}$ | $V_{IH}$ | $D_{OUT}$ |
| Write[2] | $V_{IL}$ | $V_{IH}$ | $V_{IL}$ | $D_{IN}$ |
| Standby/Write Inhibit | $V_{IH}$ | X[1] | X | High Z |
| Write Inhibit | X | X | $V_{IH}$ | |
| Write Inhibit | X | $V_{IL}$ | X | |
| Output Disable | X | $V_{IH}$ | X | High Z |
| Chip Erase | $V_{IL}$ | $V_H$ [3] | $V_{IL}$ | High Z |

Notes: 1. X can be $V_{IL}$ or $V_{IH}$.
2. Refer to A.C. Programming Waveforms.
3. $V_H = 12.0\ V \pm 0.5\ V$.

## D.C. Characteristics

| Symbol | Parameter | Condition | | Min | Max | Units |
|---|---|---|---|---|---|---|
| $I_{LI}$ | Input Load Current | $V_{IN} = 0\ V$ to $V_{CC} + 1\ V$ | | | 10 | µA |
| $I_{LO}$ | Output Leakage Current | $V_{I/O}$=0V to $V_{CC}$ | | | 10 | µA |
| $I_{SB1}$ | $V_{CC}$ Standby Current CMOS | $\overline{CE} = V_{CC}$-0.3 V to $V_{CC} + 1.0\ V$ | | | 100 | µA |
| $I_{SB2}$ | $V_{CC}$ Standby Current TTL | $\overline{CE} = 2.0\ V$ to $V_{CC} + 1.0\ V$ | Com. | | 2 | mA |
| | | | Ind., Mil. | | 3 | mA |
| $I_{CC}$ | $V_{CC}$ Active Current A.C. | f = 5 MHz; $I_{OUT}$ = 0 mA<br>$\overline{CE} = V_{IL}$ | Com. | | 30 | mA |
| | | | Ind., Mil. | | 45 | mA |
| $V_{IL}$ | Input Low Voltage | | | | 0.8 | V |
| $V_{IH}$ | Input High Voltage | | | 2.0 | | V |
| $V_{OL}$ | Output Low Voltage | $I_{OL} = 2.1\ mA$ | | | .4 | V |
| $V_{OH}$ | Output High Voltage | $I_{OH} = -400\ µA$ | | 2.4 | | V |

## Pin Capacitance (f = 1 MHz, T = 25°C) [1]

| | Typ | Max | Units | Conditions |
|---|---|---|---|---|
| $C_{IN}$ | 4 | 6 | pF | $V_{IN} = 0\ V$ |
| $C_{OUT}$ | 8 | 12 | pF | $V_{OUT} = 0\ V$ |

Note: 1. This parameter is characterized and is not 100% tested.



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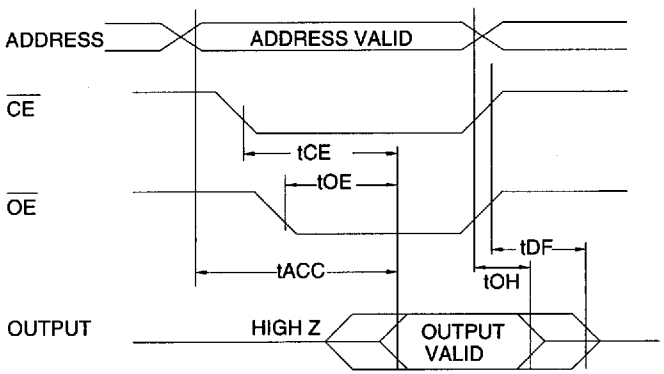
## A.C. Read Characteristics

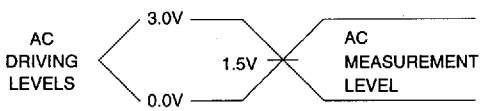
| Symbol | Parameter | AT28C16-15 | | AT28C16-20 | | AT28C16-25 | | Units |
|---|---|---|---|---|---|---|---|---|
| | | Min | Max | Min | Max | Min | Max | |
| $t_{ACC}$ | Address to Output Delay | | 150 | | 200 | | 250 | ns |
| $t_{CE}$ (1) | $\overline{CE}$ to Output Delay | | 150 | | 200 | | 250 | ns |
| $t_{OE}$ (2) | $\overline{OE}$ to Output Delay | 10 | 70 | 10 | 80 | 10 | 100 | ns |
| $t_{DF}$ (3,4) | $\overline{CE}$ or $\overline{OE}$ High to Output Float | 0 | 50 | 0 | 55 | 0 | 60 | ns |
| $t_{OH}$ | Output Hold from $\overline{OE}$, $\overline{CE}$ or Address, whichever occurred first | 0 | | 0 | | 0 | | ns |

## A.C. Read Waveforms(1,2,3,4)



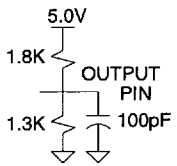

Notes:
1. $\overline{CE}$ may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on $t_{ACC}$.
2. $\overline{OE}$ may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on $t_{CE}$ or by $t_{ACC} - t_{OE}$ after an address change without impact on $t_{ACC}$.
3. $t_{DF}$ is specified from $\overline{OE}$ or $\overline{CE}$ whichever occurs first ($C_L$ = 5 pF).
4. This parameter is characterized and is not 100% tested.

## Input Test Waveforms and Measurement Level




$t_R$, $t_F$ < 20 ns

## Output Test Load



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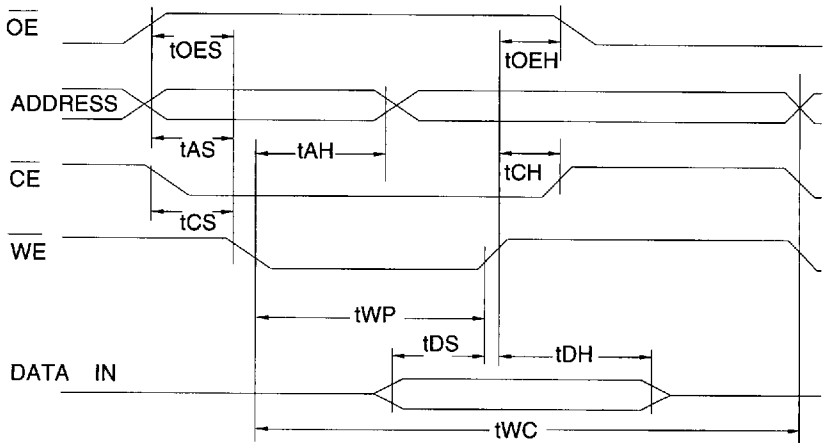
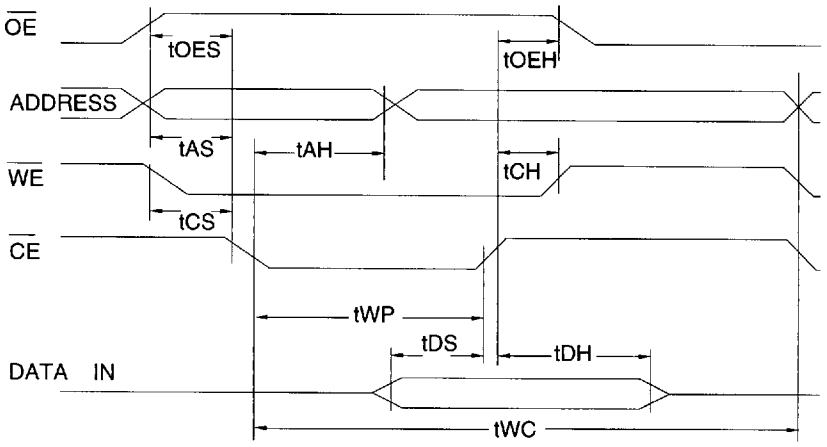
## A.C. Write Characteristics

| Symbol | Parameter | | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| $t_{AS}$, $t_{OES}$ | Address, $\overline{OE}$ Set-up Time | | 10 | | | ns |
| $t_{AH}$ | Address Hold Time | | 50 | | | ns |
| $t_{WP}$ | Write Pulse Width ($\overline{WE}$ or $\overline{CE}$) | | 100 | | 1000 | ns |
| $t_{DS}$ | Data Set-up Time | | 50 | | | ns |
| $t_{DH}$,$t_{OEH}$ | Data, $\overline{OE}$ Hold Time | | 10 | | | ns |
| $t_{CS}$,$t_{CH}$ | $\overline{CE}$ to $\overline{WE}$ and $\overline{WE}$ to $\overline{CE}$ Set-up and Hold Time | | 0 | | | ns |
| $t_{WC}$ | Write Cycle Time | AT28C16 | | 0.5 | 1.0 | ms |
| | | AT28C16E | | 100 | 200 | µs |

## A.C. Write Waveforms- $\overline{WE}$ Controlled




## A.C. Write Waveforms- $\overline{CE}$ Controlled



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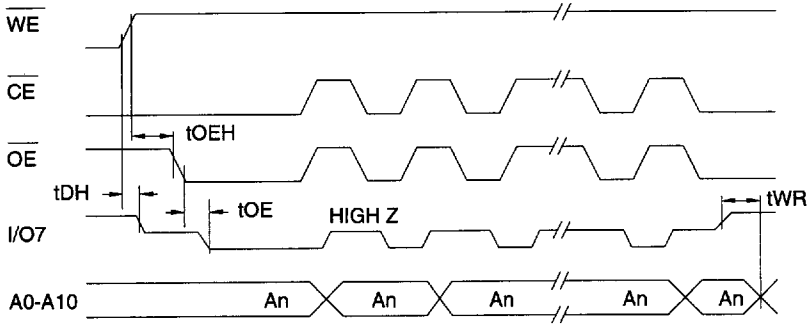
## $\overline{\text{Data}}$ Polling Characteristics[1]

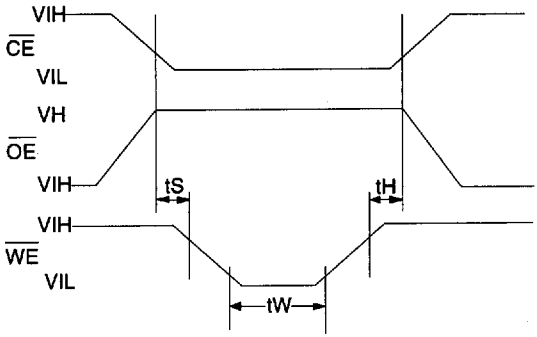
| Symbol | Parameter | Min | Typ | Max | Units |
|---|---|---|---|---|---|
| $t_{DH}$ | Data Hold Time | 10 | | | ns |
| $t_{OEH}$ | $\overline{OE}$ Hold Time | 10 | | | ns |
| $t_{OE}$ | $\overline{OE}$ to Output Delay[2] | | | | ns |
| $t_{WR}$ | Write Recovery Time | 0 | | | ns |

Notes: 1. These parameters are characterized and not 100% tested.
2. See A.C. Characteristics.

## $\overline{\text{Data}}$ Polling Waveforms




## Chip Erase Waveforms




$t_S = t_H = 1$ µsec (min.)
$t_W = 10$ msec (min.)
$V_H = 12.0\ V \pm 0.5\ V$



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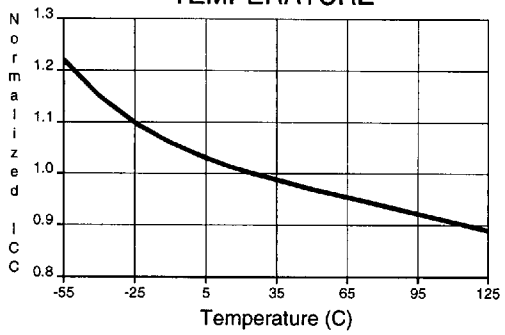
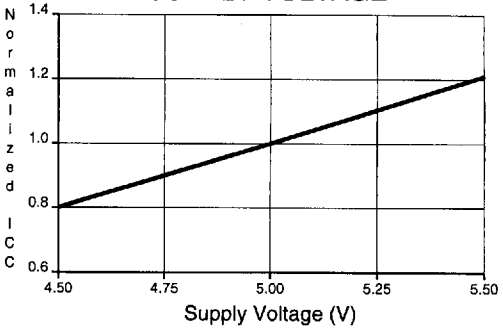
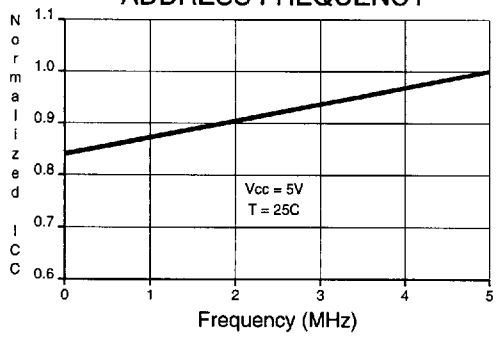
## NORMALIZED SUPPLY CURRENT vs. TEMPERATURE



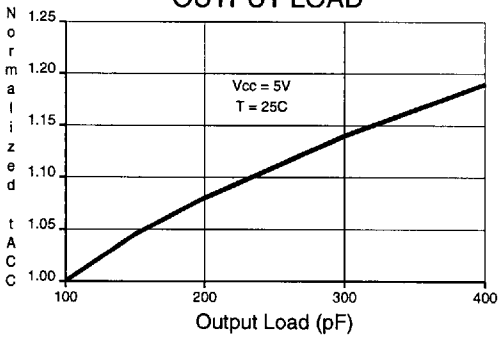

## NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



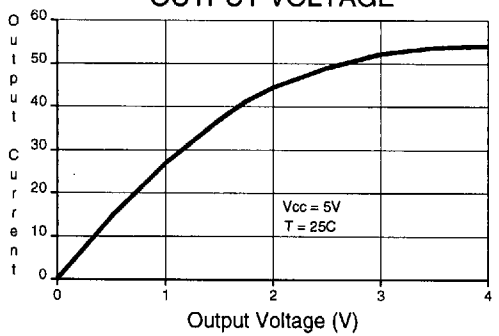

## NORMALIZED SUPPLY CURRENT vs. ADDRESS FREQUENCY



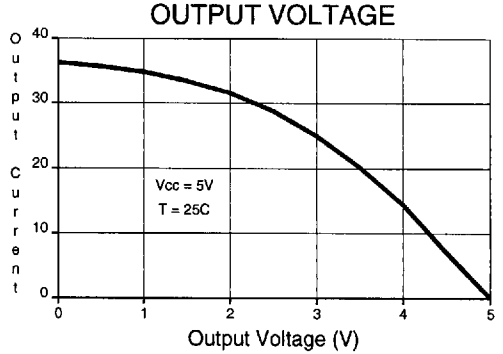

## NORMALIZED ACCESS TIME vs. OUTPUT LOAD




## OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE




## OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



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## Ordering Information[1]

| $t_{ACC}$ (ns) | $I_{CC}$ (mA) | | Ordering Code | Package | Operation Range |
|---|---|---|---|---|---|
| | Active | Standby | | | |
| 150 | 30 | 0.1 | AT28C16(E)-15DC<br>AT28C16(E)-15JC<br>AT28C16(E)-15PC<br>AT28C16(E)-15SC | 24D6<br>32J<br>24P6<br>24S | Commercial<br>(0°C to 70°C) |
| 150 | 45 | 0.1 | AT28C16(E)-15JI<br>AT28C16(E)-15PI<br>AT28C16(E)-15SI | 32J<br>24P6<br>24S | Industrial<br>(-40°C to 85°C) |
| | | | AT28C16(E)-15DM/883 | 24D6 | Military/883C<br>Class B, Fully Compliant<br>(-55°C to 125°C) |
| 200 | 30 | 0.1 | AT28C16(E)-20DC<br>AT28C16(E)-20JC<br>AT28C16(E)-20PC<br>AT28C16(E)-20SC | 24D6<br>32J<br>24P6<br>24S | Commercial<br>(0°C to 70°C) |
| 200 | 45 | 0.1 | AT28C16(E)-20JI<br>AT28C16(E)-20PI<br>AT28C16(E)-20SI | 32J<br>24P6<br>24S | Industrial<br>(-40°C to 85°C) |
| | | | AT28C16(E)-20DM/883 | 24D6 | Military/883C<br>Class B, Fully Compliant<br>(-55°C to 125°C) |
| 250 | 30 | 0.1 | AT28C16(E)-25DC<br>AT28C16(E)-25JC<br>AT28C16(E)-25PC<br>AT28C16(E)-25SC<br>AT28C16-W | 24D6<br>32J<br>24P6<br>24S<br>DIE | Commercial<br>(0°C to 70°C) |
| 250 | 45 | 0.1 | AT28C16(E)-25JI<br>AT28C16(E)-25PI<br>AT28C16(E)-25SI | 32J<br>24P6<br>24S | Industrial<br>(-40°C to 85°C) |
| | | | AT28C16(E)-25DM/883 | 24D6 | Military/883C<br>Class B, Fully Compliant<br>(-55°C to 125°C) |

Note: 1. See valid Part Number table below.

## Valid Part Numbers

The following table lists standard Atmel products that can be ordered.

| Device Numbers | Speed | Package and Temperature Combinations |
|---|---|---|
| **AT28C16** | 15 | DC, JC, JI, PC, PI, SC, SI, DM/883 |
| **AT28C16E** | 15 | DC, JC, JI, PC, PI, SC, SI, DM/883 |
| **AT28C16** | 20 | DC, JC, JI, PC, PI, SC, SI, DM/883 |
| **AT28C16E** | 20 | DC, JC, JI, PC, PI, SC, SI, DM/883 |
| **AT28C16** | 25 | DC, JC, JI, PC, PI, SC, SI, DM/883 |
| **AT28C16E** | 25 | DC, JC, JI, PC, PI, SC, SI, DM/883 |



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## Ordering Information

| Package Type | |
|---|---|
| **24D6** | 24 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip) |
| **32J** | 32 Lead, Plastic J-Leaded Chip Carrier (PLCC) |
| **24P6** | 24 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP) |
| **24S** | 24 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC) |
| **W** | Die |
| **Options** | |
| **Blank** | Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms |
| **E** | High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 µs |





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